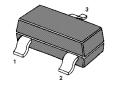
## SILICON EPITAXIAL SCHOTTKY BARRIER DIODE

For low voltage high speed switching application

## **Features**

- Low forward voltage
- Low reverse current





Marking Code: "ZD" SOT-23 Plastic Package

Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)

| Parameter  | Symbol           | Value         | Unit |
|--|------------------|---------------|------|
| Maximum Peak Reverse Voltage                           | $V_{RM}$         | 45            | V    |
| Reverse Voltage  | V <sub>R</sub>   | 40            | V    |
| Average Forward Current                                | Io               | 100           | mA   |
| Maximum Peak Forward Current                           | I <sub>FM</sub>  | 300           | mA   |
| Non-Repetitive Peak Forward Surge Current ( t = 10 ms) | I <sub>FSM</sub> | 1             | А    |
| Power Dissipation                                      | P <sub>d</sub>   | 150           | mW   |
| Junction Temperature                                   | T <sub>j</sub>   | 125           | °C   |
| Storage Temperature Range                              | T <sub>stg</sub> | - 55 to + 125 | °C   |

## Characteristics at T<sub>a</sub> = 25 °C

| Parameter                                     | Symbol         | Min. | Max. | Unit |
|---|----------------|------|------|------|
| Forward Voltage at I <sub>F</sub> = 100 mA    | V <sub>F</sub> | -    | 0.6  | V    |
| Reverse Current at V <sub>R</sub> = 40 V      | I <sub>R</sub> | -    | 5    | μΑ   |
| Reverse Breakdown Voltage at $I_R = 10 \mu A$ | $V_{(BR)R}$    | 45   | -    | ٧    |
| Total Capacitance at $V_R = 0$ , $f = 1$ MHz  | Ст             | -    | 25   | pF   |

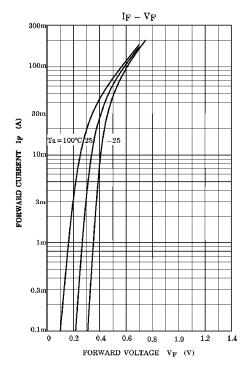


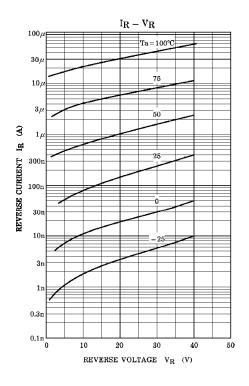


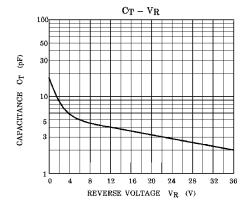


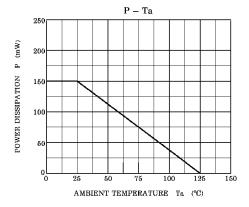


Dated: 04/12/2007













(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)







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